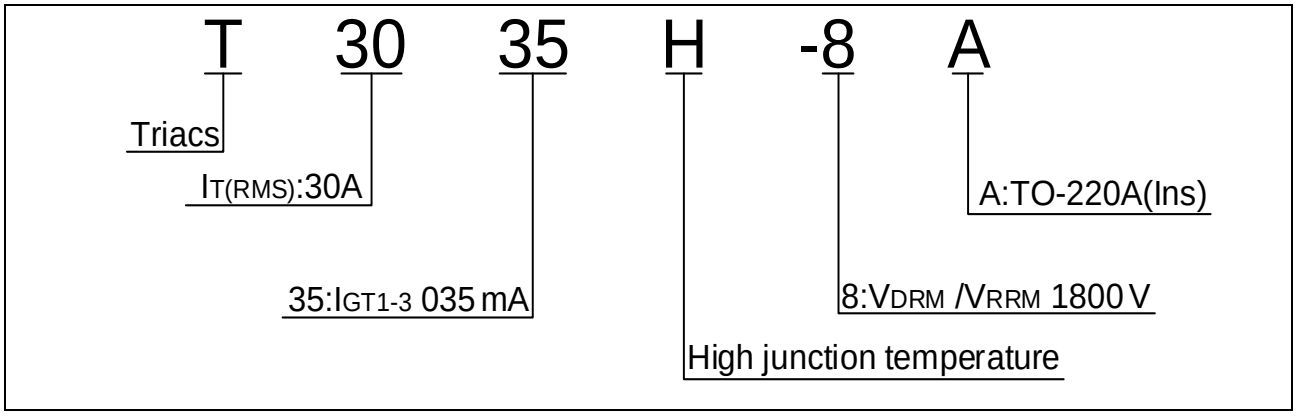
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D = V_{DRM} T_j =150 R_L =3.3k	- -	MIN.	0.15	V
I_L	I_G =1.2I_{GT}	-			

ORDERING INFORMATION

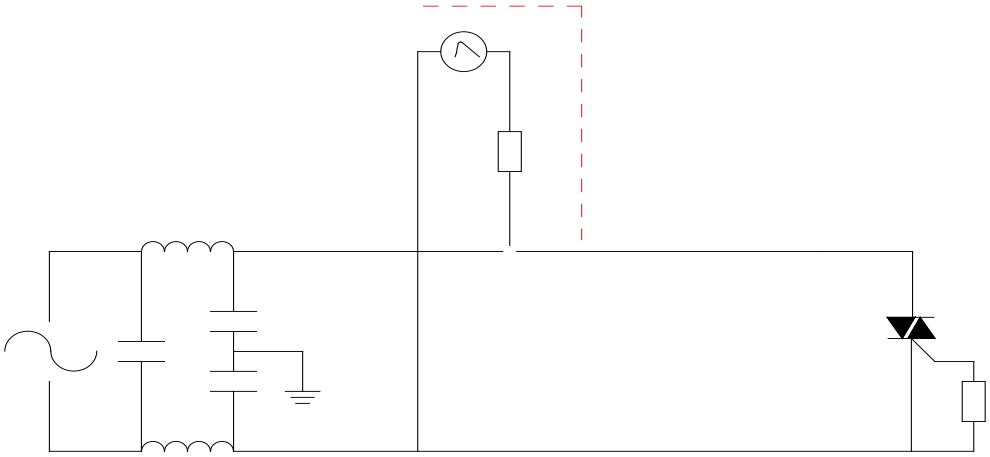


MARKING

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	

PACKAGE MECHANICAL DATA

